

BUK7606-55B

N-channel TrenchMOS standard level FET Rev. 02 — 21 June 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids



1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|---|------------|-----|-----|-----|------|
| V_{DS} | drain-source voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ | | - | - | 55 | V |
| I _D | drain current | $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u> | <u>[1]</u> | - | - | 75 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 254 | W |
| Static cha | racteristics | | | | | | |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u> | | - | 5.1 | 6 | mΩ |
| Avalanche | ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 75 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped | | - | - | 680 | mJ |
| Dynamic o | characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 44 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 13 | | - | 19 | - | nC |

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1 | G | gate | | |
| 2 | D | drain[1] | mb | D |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | SOT404 (D2PAK) | |

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BUK7606-55B | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

BUK7606-55B

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4. Limiting values

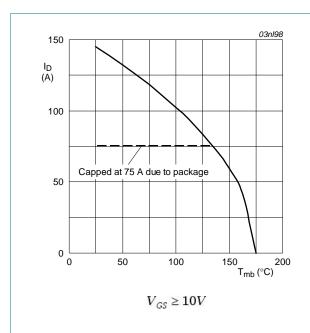
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|--|------------|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 55 | V |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20 \text{ k}\Omega$ | | - | - | 55 | V |
| V_{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 3</u> ; see <u>Figure 1</u> | <u>[1]</u> | - | - | 145 | Α |
| | | $T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see} \frac{\text{Figure 1}}{}$ | [2] | - | - | 75 | Α |
| | | T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u> | [2] | - | - | 75 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; t_p ≤ 10 μs; pulsed; see Figure 3 | | - | - | 582 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 254 | W |
| T _{stg} | storage temperature | | | -55 | - | 175 | °C |
| Tj | junction temperature | | | -55 | - | 175 | °C |
| Source-drain | diode | | | | | | |
| Is | source current | T _{mb} = 25 °C | <u>[1]</u> | - | - | 145 | Α |
| | | | [2] | - | - | 75 | Α |
| I _{SM} | peak source current | $t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$ | | - | - | 582 | Α |
| Avalanche ru | iggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 75 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped | | - | - | 680 | mJ |
| | | | | | | | |

^[1] Current is limited by power dissipation chip rating.

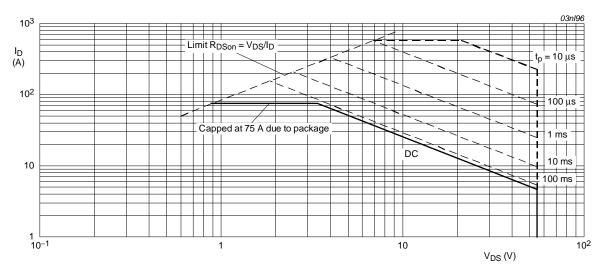
^[2] Continuous current is limited by package.



P_{der} (%) 80 40 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 1. Normalized continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|---|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | see Figure 4 | - | - | 0.59 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint; mounted on a printed-circuit board | - | - | 50 | K/W |

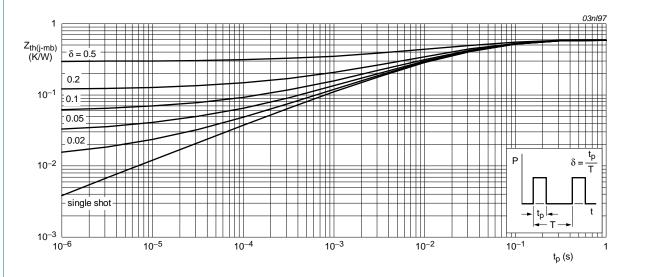


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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BUK7606-55B

Characteristics

Table 6. Characteristics

| Table 6. | Characteristics | | | | | |
|---------------------|----------------------------------|---|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | 55 | - | - | V |
| | breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$ | 50 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 10</u> | - | - | 4.4 | V |
| | | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 10 | 2 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 10 | 1 | - | - | V |
| I _{DSS} | drain leakage current | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.02 | 1 | μΑ |
| | | V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μΑ |
| I _{GSS} | gate leakage current | $V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 2 | 100 | nA |
| | | $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$ | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 11</u> ; see <u>Figure 12</u> | - | - | 12 | mΩ |
| | | V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | 5.1 | 6 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 25 \text{ A}; \ V_{DS} = 44 \text{ V}; \ V_{GS} = 10 \text{ V};$ | - | 64 | - | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C; see <u>Figure 13</u> | - | 14 | - | nC |
| Q_{GD} | gate-drain charge | | - | 19 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ | - | 3825 | 5100 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 14</u> | - | 783 | 940 | pF |
| C _{rss} | reverse transfer capacitance | | - | 235 | 322 | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \Omega; T_j = 25 ^{\circ}C$ | - | 30 | - | ns |
| t _r | rise time | $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \Omega; T_j = 30 ^{\circ}C$ | - | 46 | - | ns |
| t _{d(off)} | turn-off delay time | $V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$ | - | 85 | - | ns |
| t _f | fall time | $R_{G(ext)} = 10 \Omega$; $T_j = 25 °C$ | - | 39 | - | ns |
| L _D | internal drain inductance | from drain lead 6 mm from package to centre of die; T _j = 25 °C | - | 4.5 | - | nΗ |
| | | from upper edge of drain mounting base to centre of die; T _i = 25 °C | - | 2.5 | - | nΗ |
| L _S | internal source inductance | from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$ | - | 7.5 | - | nΗ |
| Source-di | ain diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 15</u> | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; | - | 73 | - | ns |
| Q _r | recovered charge | $V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$ | - | 82 | - | nC |

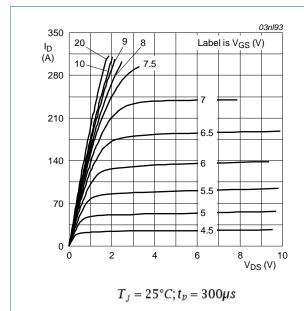


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

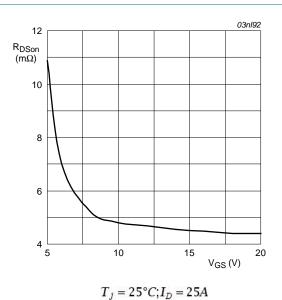


Fig 6. Drain-source on-state resistance as a function

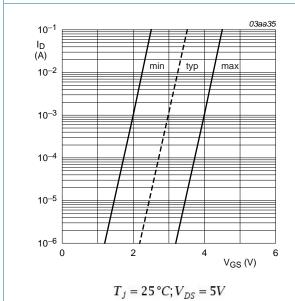


Fig 7. Sub-threshold drain current as a function of gate-source voltage

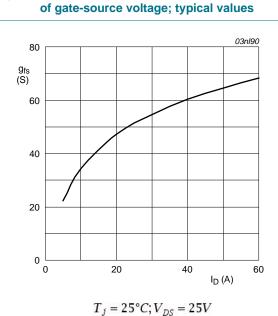


Fig 8. Forward transconductance as a function of drain current; typical values

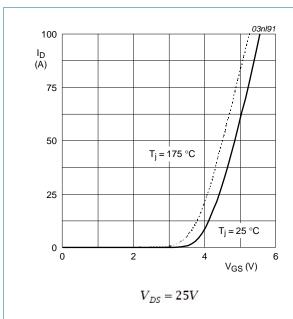


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

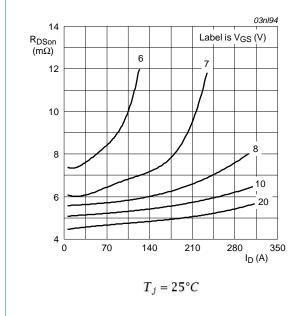
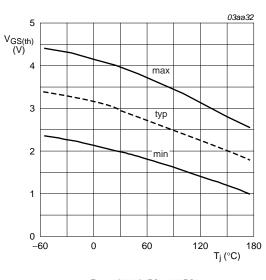


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1 mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

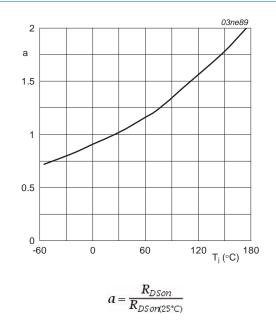


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

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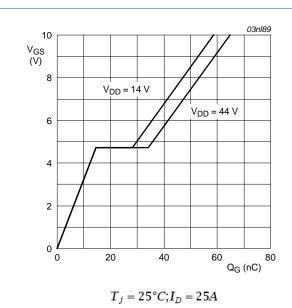
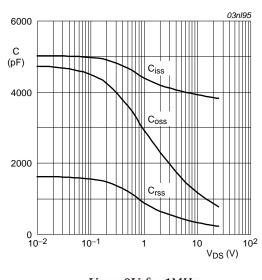


Fig 13. Gate-source voltage as a function of turn-on gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

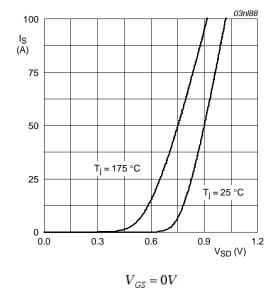


Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

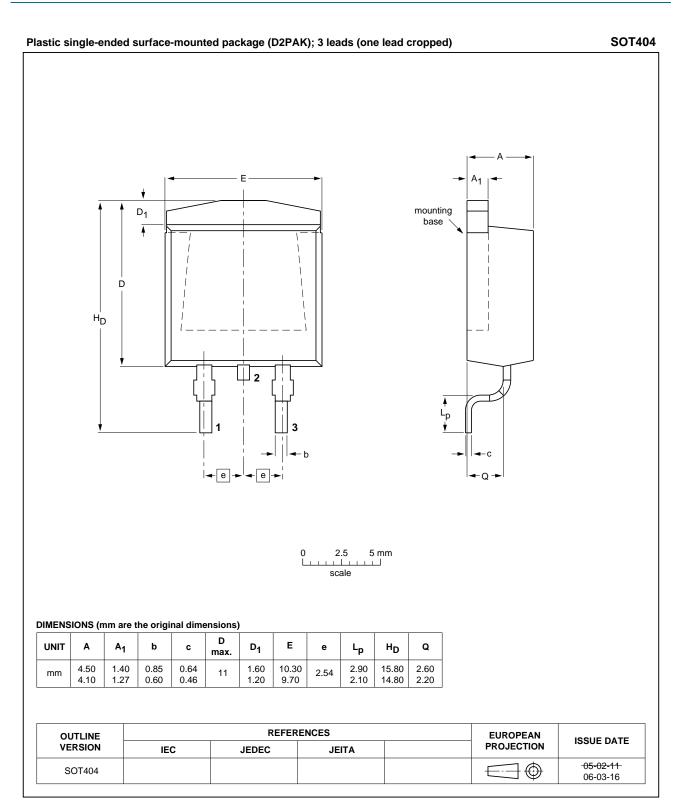


Fig 16. Package outline SOT404 (D2PAK)

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Revision history

Table 7. **Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|--------------------|---|--------------------------|-------------------------|--------------------|
| BUK7606-55B v.2 | 20100621 | Product data sheet | - | BUK75_7606_55B v.1 |
| Modifications: | The format of this data sheet has been redesigned to comply with the new identity of of NXP Semiconductors. | | | |
| | Legal texts | have been adapted to the | new company name wh | ere appropriate. |
| | Type numb | er BUK7606-55B separat | ed from data sheet BUK7 | 5_7606_55B v.1. |
| BUK75_7606_55B v.1 | 20030331 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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N-channel TrenchMOS standard level FET

11. Contents

| 1 | Product profile |
|-----|--------------------------|
| 1.1 | General description |
| 1.2 | Features and benefits1 |
| 1.3 | Applications1 |
| 1.4 | Quick reference data2 |
| 2 | Pinning information2 |
| 3 | Ordering information2 |
| 4 | Limiting values3 |
| 5 | Thermal characteristics5 |
| 6 | Characteristics6 |
| 7 | Package outline |
| 8 | Revision history11 |
| 9 | Legal information12 |
| 9.1 | Data sheet status |
| 9.2 | Definitions12 |
| 9.3 | Disclaimers |
| 9.4 | Trademarks13 |
| 40 | Contact information 12 |

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